

TRANSISTOR(PNP)

FEATURES

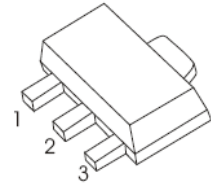
- Small Flat Package
- LF Amplifier, Electronic Governor Applications

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-50\text{mA}$	100		560	
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1.2	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		25		pF
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-50\text{mA}$		180		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	R	S	T	U
RANGE	100 - 200	140 - 280	200 - 400	280 - 560
MARKING	BB			